1. General description

Planar passivated ultra sensitive gate Silicon Controlled Rectifier in a SOT54 (T0-92) plastic package.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Ultra sensitive gate

3. Applications

- Electronic ballasts
- · Safety shut down and protection circuits
- Sensing circuits
- Smoke detectors
- Switched Mode Power Supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage			-	-	400	V
V_{RRM}	repetitive peak reverse voltage			-	-	400	V
I _{TSM}	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 10 \text{ms}$; Fig. 4; Fig. 5		-	-	8	Α
I _{T(AV)}	average on-state current	half sine wave; T _{lead} ≤ 92 °C; <u>Fig. 1</u>		-	-	0.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; $T_{lead} \le 92$ °C; Fig. 2; Fig. 3		-	-	0.8	Α
Static characteristics							,
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 7		-	3	12	μΑ

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5. Pinning information

Table 2. Pinning information

1 A anode 2 G gate 3 K cathode	Pin	Symbol	Description	Simplified outline	Graphic symbol
3 K cathode	1	Α	anode		A
3 K cathode	2	G	gate		_
3 2 1 TO-92 (SOT54)	3	K	cathode	-	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
EC103D1 TO-92		plastic single-ended leaded (through hole) package; 3 leads	SOT54			

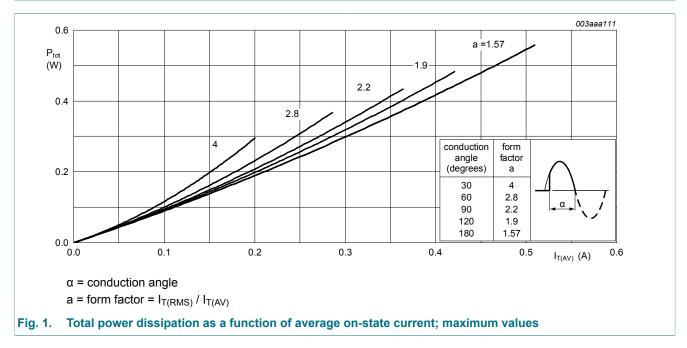
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7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	400	V
V_{RRM}	repetitive peak reverse voltage		-	400	V
I _{T(AV)}	average on-state current	half sine wave; T _{lead} ≤ 92 °C; <u>Fig. 1</u>	-	0.5	Α
I _{T(RMS)}	RMS on-state current	half sine wave; T _{lead} ≤ 92 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	0.8	A
I _{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	-	8	A
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 8.3 ms$	-	9	A
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	$I_T = 2 \text{ A}; I_G = 10 \text{ mA}; dI_G/dt = 100 \text{ mA/}$ µs	-	50	A/µs
I _{GM}	peak gate current		-	1	Α
V_{RGM}	peak reverse gate voltage		-	5	V
P _{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



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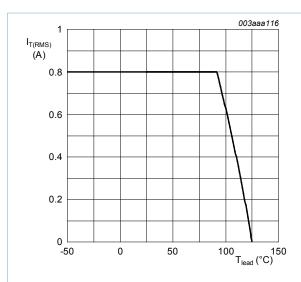
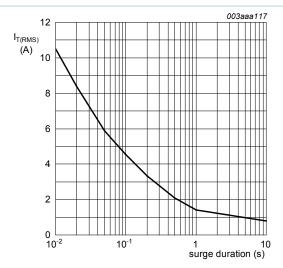
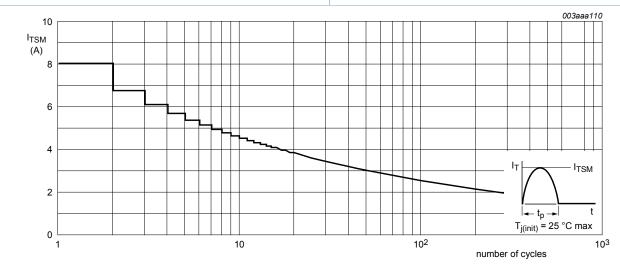


Fig. 2. RMS on-state current as a function of lead temperature; maximum values



f = 50 Hz; T_{lead} = 92 °C

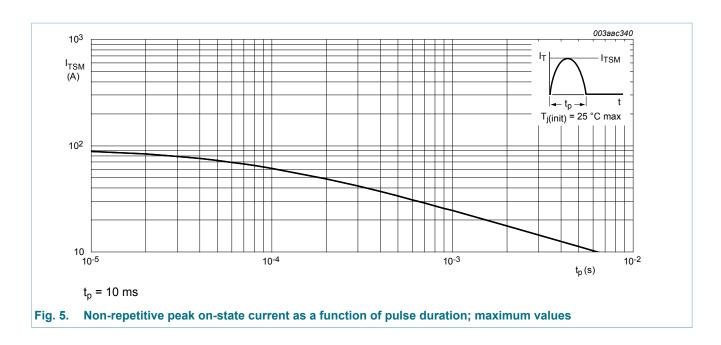
Fig. 3. RMS on-state current as a function of surge duration; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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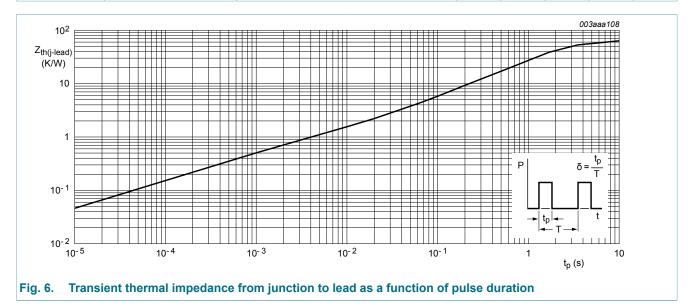


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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-lead)}	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



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9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 \text{ °C};$ Fig. 7	-	3	12	μA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.5 \text{ mA}; R_{GK} = 1 \text{ k}\Omega;$ $T_j = 25 \text{ °C}; Fig. 8$	-	2	6	mA
l _H	holding current	$V_D = 12 \text{ V}; \text{ R}_{GK} = 1 \text{ k}\Omega; \text{ T}_j = 25 \text{ °C};$ Fig. 9	-	2	5	mA
V_{T}	on-state voltage	I _T = 1 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.2	1.35	V
V _{GT} gate trigg	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C};$ Fig. 11	-	0.5	0.8	V
		$V_D = 400 \text{ V}; I_T = 10 \text{ mA}; T_j = 125 ^{\circ}\text{C};$ Fig. 11	0.2	0.3	-	V
I _D	off-state current	$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
I _R	reverse current	$V_R = 400 \text{ V}; T_j = 125 \text{ °C}; R_{GK} = 1 \text{ k}\Omega$	-	0.05	0.1	mA
Dynamic c	haracteristics		<u> </u>			
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 125 °C; R_{GK} = 1 kΩ; (V_{DM} = 67% of V_{DRM}); exponential waveform; Fig. 12	-	150	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 2 A; V_D = 400 V; I_G = 10 mA; $dI_G/$ dt = 0.1 A/ μ s; T_j = 25 °C	-	2	-	μs
t _q	commutated turn-off time	V_{DM} = 268 V; T_j = 125 °C; I_{TM} = 1.6 A; V_R = 35 V; $(dI_T/dt)_M$ = 30 A/ μ s; dV_D/dt = 2 V/ μ s; R_{GK} = 1 k Ω ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

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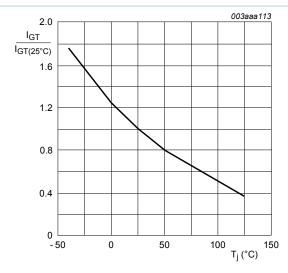


Fig. 7. Normalized gate trigger current as a function of junction temperature

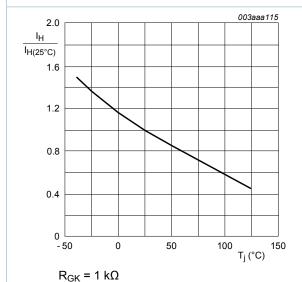
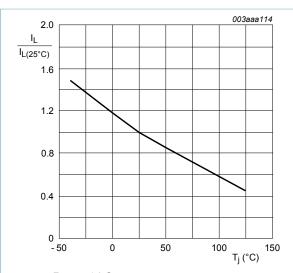
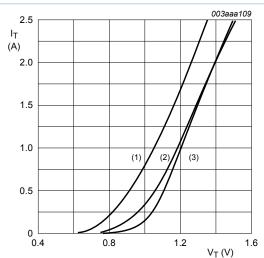


Fig. 9. Normalized holding current as a function of junction temperature



 $R_{GK} = 1 k\Omega$

Fig. 8. Normalized latching current as a function of junction temperature



 $V_0 = 0.895 \text{ V}; R_s = 0.195 \Omega$

(1) T_i = 125 °C; typical values

(2) T_i = 125 °C; maximum values

(3) T_i = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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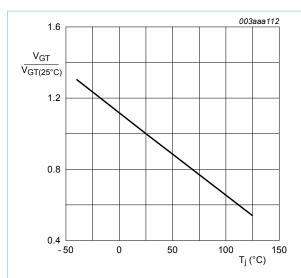


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

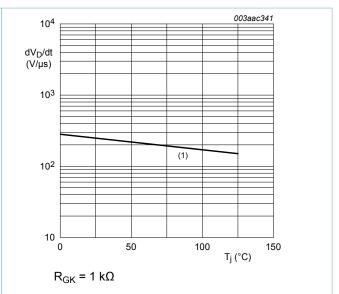
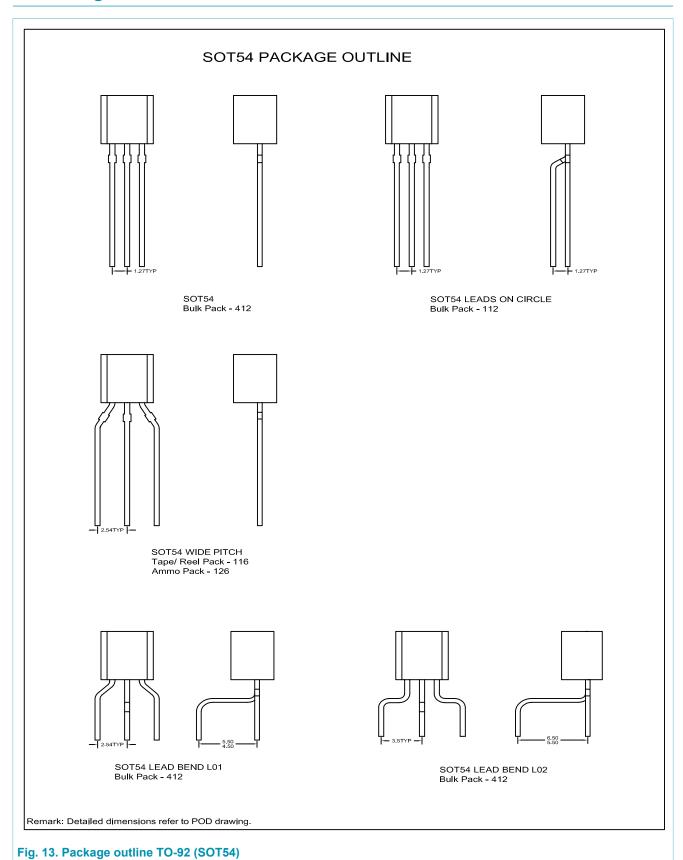


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline



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11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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